

ABSTRACT OF THE DISCLOSURE

A magnetic memory includes: a magnetoresistance effect element having a magnetic recording layer; a first wiring extending in a first direction on or below the magnetoresistance effect element; a covering layer provided at least both sides of the first wiring, the covering layer being made of magnetic material, and the covering layer having a uniaxial anisotropy in the first direction along which a magnetization of the covering layer occurs easily; and a writing circuit configured to pass a current through the first wiring in order to record an information in the magnetic recording layer by a magnetic field generated by the current.